

SOT223 NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTOR

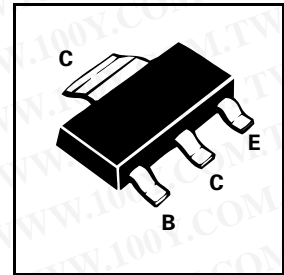
FZT603

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FEATURES

- * 2A continuous current
- * Useful h_{FE} up to 6A
- * Fast Switching

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)



PARTMARKING DETAIL – DEVICE TYPE IN FULL

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	10	V
Peak Pulse Current	I_{CM}	6	A
Continuous Collector Current	I_C	2	A
Power Dissipation	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100	240		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80	110		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10	16		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			0.01 10	μA μA	$V_{CB}=80\text{V}$ $V_{CB}=80\text{V}, T_{amb}=100^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=8\text{V}$
Collector Cut-Off Current	I_{CES}			10	μA	$V_{CES}=80\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.79 0.80 0.88 0.99 0.86	0.88 0.90 1.00 1.13	V V V V V	$I_C=0.25\text{A}, I_B=0.25\text{mA}^*$ $I_C=0.4\text{A}, I_B=0.4\text{mA}^*$ $I_C=1\text{A}, I_B=1\text{mA}^*$ $I_C=2\text{A}, I_B=20\text{mA}^*$ $I_C=2\text{A}, I_B=20\text{mA}$ †

† $T_j=150^\circ\text{C}$

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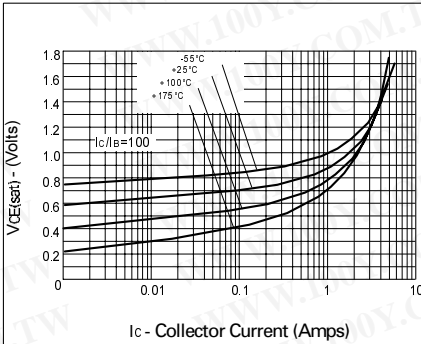
ELECTRICAL CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.7	1.95	V	$I_C=2A, I_B=20mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		1.5	1.75	V	$I_C=2A, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	h_{FE}	3k 5k 3k 2k	14k 15k 14k 10k 2k 750	100k		$I_C=50mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$ $I_C=1A, V_{CE}=5V^*$ $I_C=2A, V_{CE}=5V^*$ $I_C=5A, V_{CE}=5V^*$ $I_C=6A, V_{CE}=5V^*$
Transition Frequency	f_T	150			MHz	$I_C=100mA, V_{CE}=10V$ $f=20MHz$
Output Capacitance	C_{ibo}		90		pF	$V_{EB}=500mV, f=1MHz$
Output Capacitance	C_{obo}		15		pF	$V_{CB}=10V, f=1MHz$
Switching Times	t_{on}		0.5		μs	$I_C=0.5A, V_{CE}=10V$ $I_{B1}=I_{B2}=0.5mA$
	t_{off}		1.6		μs	

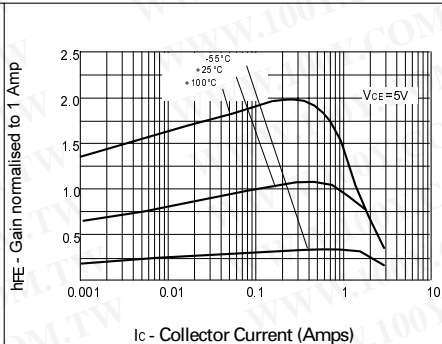
*Measured under pulsed conditions. Pulse width=300ms. Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

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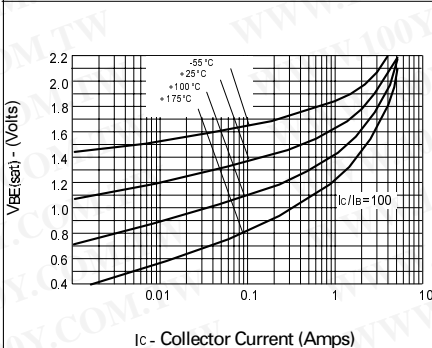
TYPICAL CHARACTERISTICS



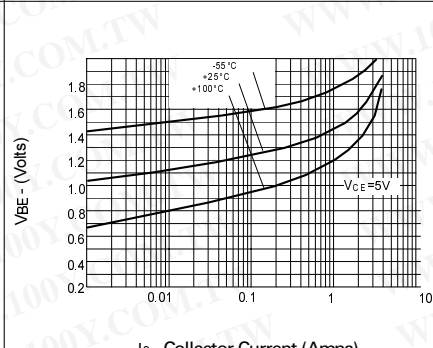
$V_{CE(sat)}$ v I_C



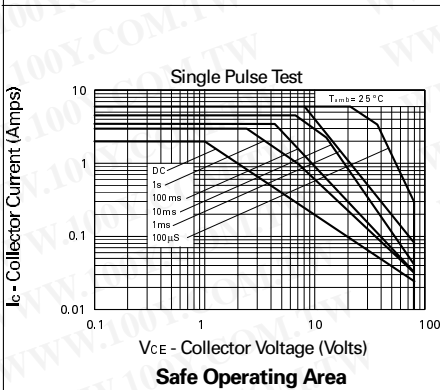
hFE v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



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